

2SC4706

Silicon NPN Triple Diffused Planar Transistor (High Voltage Switching Transistor)

Application : Switching Regulator and General Purpose

Absolute maximum ratings (Ta=25°C)

Symbol	Ratings	Unit
V _{CB0}	900	V
V _{CEO}	600	V
V _{EB0}	7	V
I _C	14(Pulse28)	A
I _B	7	A
P _C	130(T _C =25°C)	W
T _j	150	°C
T _{stg}	-55to+150	°C

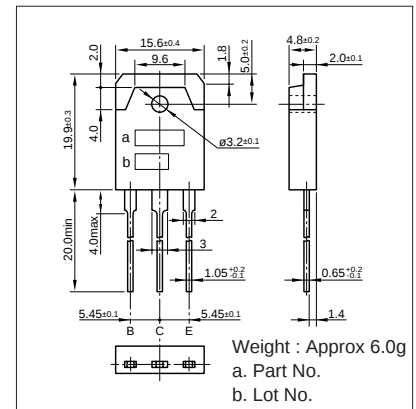
Electrical Characteristics (Ta=25°C)

Symbol	Conditions	Ratings	Unit
I _{CBO}	V _{CB} =800V	100max	μA
I _{EBO}	V _{EB} =7V	100max	μA
V _{(BR)CEO}	I _C =10mA	600min	V
h _{FE}	V _{CE} =4V, I _C =7A	10to25	
V _{CE(sat)}	I _C =7A, I _B =1.4A	0.5max	V
V _{BE(sat)}	I _C =7A, I _B =1.4A	1.2max	V
f _r	V _{CE} =12V, I _E =-1.5A	6typ	MHz
C _{OB}	V _{CB} =10V, f=1MHz	160typ	pF

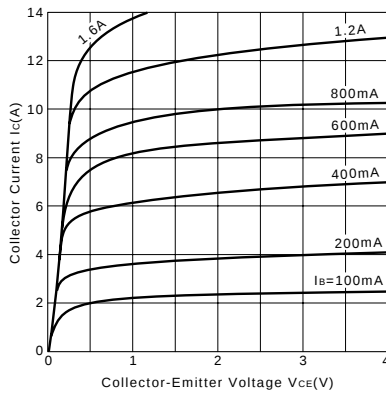
Typical Switching Characteristics (Common Emitter)

V _{CC} (V)	R _L (Ω)	I _C (A)	V _{BB1} (V)	V _{BB2} (V)	I _{B1} (A)	I _{B2} (A)	t _{on} (μs)	t _{stg} (μs)	t _f (μs)
250	35.7	7	10	-5	1.05	-3.5	1max	5max	0.7max

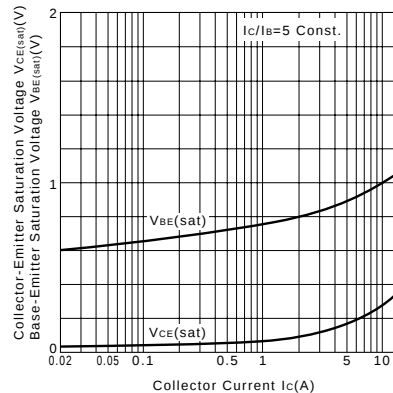
External Dimensions MT-100(TO3P)



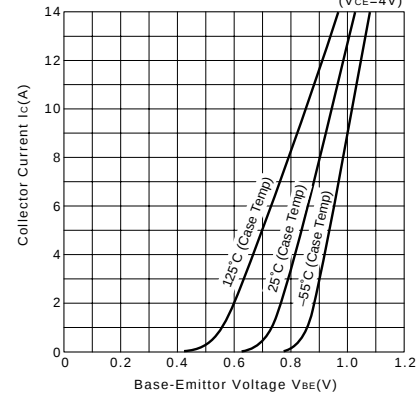
I_C-V_{CE} Characteristics (Typical)



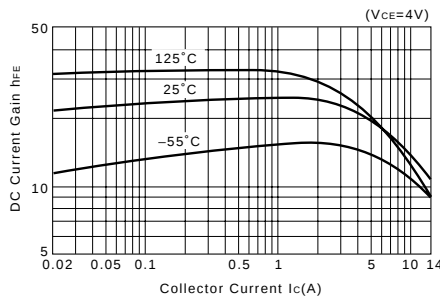
V_{CE(sat)}, V_{BE(sat)}-I_C Temperature Characteristics (Typical)



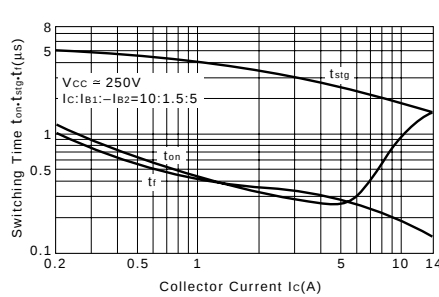
I_C-V_{BE} Temperature Characteristics (Typical)



h_{FE}-I_C Temperature Characteristics (Typical)

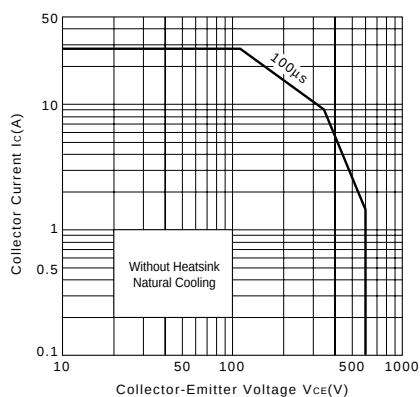


t_{on}•t_{stg}•t_f-I_C Characteristics (Typical)

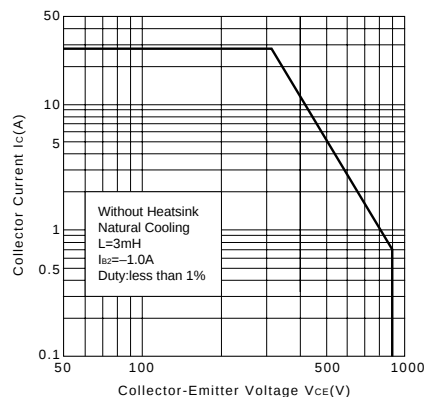


θ_{j-a}-t Characteristics

Safe Operating Area (Single Pulse)



Reverse Bias Safe Operating Area



P_C-T_a Derating

